SGS-THOMSON MICROELECTRONICS

TGAL 602 → 610

TRIACS

- GLASS PASSIVATED CHIP
- I_{GT} SPECIFIED IN FOUR QUADRANTS

ADVANTAGES

- EXCELLENT $(dv/dt)_c$: > 10 V/µs
- METALLIC ENCAPSULATION GIVES AN EXCELLENT THERMAL IMPEDANCE AND HIGH RELIABILITY CONSTRUCTION

APPLICATIONS

- MOTOR CONTROL
- HEATING CONTROL
- LIGHT DIMMER

TO 65
(Metal)

DESCRIPTION

Power triacs suited for use on 220 V and 380 V main.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state Current (360° conduction angle)	T_C = 75 °C	60	A
I_{TSM}	Non Repetitive Surge Peak on-state Current (T_j initial = 25 °C - Half sine wave)	t = 8.3 ms	550	A
		t = 10 ms	500	
I^2t	I^2t Value for Fusing	t = 10 ms	1250	A^2s
di/dt	Critical Rate of Rise of on-state Current (1)	Repetitive F = 50 Hz	50	A/µs
		Non Repetitive	300	
T_{stg} T_j	Storage and Operating Junction Temperature Range		− 40 to 150 − 40 to 125	°C °C

Symbol	Parameter	TGAL					Unit
		602	604	606	608	610	
V_{DRM}	Repetitive Peak off-state Voltage (2)	200	400	600	800	1000	V

(1) I_G = 1.5 A di_G/dt = 1 A/µs
(2) T_j = 125 °C.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th\ (c-h)}$	Contact (case-heatsink) for Recommended Stud Torque	0.3	°C/W
$R_{th\ (j-c)}$ DC	Junction to Case for DC	0.66	°C/W
$R_{th\ (j-c)}$ AC	Junction to Case for 360 ° Conduction Angle (F = 50 Hz)	0.5	°C/W

GATE CHARACTERISTICS (maximum values)

P_{GM} = 40 W (t_p = 10 µs) I_{GM} = 6 A (t_p = 10 µs)

$P_{G(AV)}$ = 1 V V_{GM} = 16 V (t_p = 10 µs)

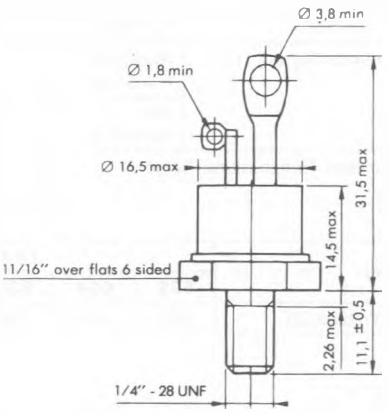
ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	R_L = 33 Ω	I-III			100	mA
				II-IV			150	
V_{GT}	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	R_L = 33 Ω	I-II-III-IV			1.5	V
V_{GD}	T_j = 125 °C	$V_D = V_{DRM}$	R_L = 3.3 kΩ	I-II-III-IV	0.2			V
I_H*	T_j = 25 °C	I_T = 500 mA	Gate Open				100	mA
I_L	T_j = 25 °C Pulse Duration > 20 µs	V_D = 12 V	I_G = 300 mA	I-III-IV		60		mA
				II		120		
V_{TM}*	T_j = 25 °C	I_{TM} = 100 A	t_p = 10 ms				2	V
I_{DRM}*	T_j = 125 °C	V_{DRM} Specified					10	mA
dv/dt*	T_j = 125 °C Linear Slope up to V_D = 67 % V_{DRM}	Gate Open			250			V/µs
$(dv/dt)_c$*	T_C = 75 °C $(di/dt)_c$ = 26.7 A/ms	$V_D = V_{DRM}$	I_T = 100 A		10			V/µs
t_{gt}	T_j = 25 °C I_G = 500 mA	$V_D = V_{DRM}$ di_G/dt = 3.5 A/µs	I_T = 100 A	I-II-III-IV		3		µs

* For either polarity of electrode A_2 voltage with reference to electrode A_1.

PACKAGE MECHANICAL DATA

TO 65 Metal



Cooling method : by conduction (method C)
Marking : type number
Weight : 19 g without accessories
Polarity : Electrode A_2 to case
Stud torque : 3.5 mAN min - 3.8 mAN max.

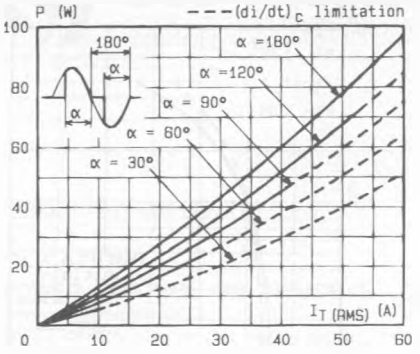


Fig.1 - Maximum mean power dissipation versus RMS on-state current (F = 60 Hz).

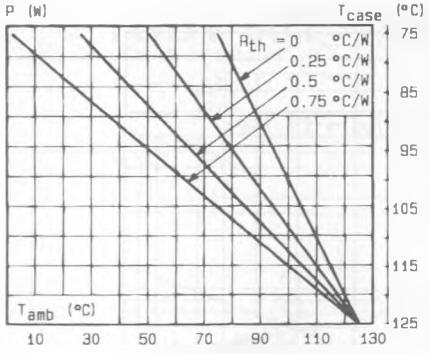


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

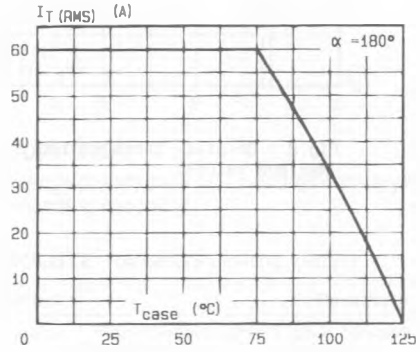


Fig.3 - RMS on-state current versus case temperature.

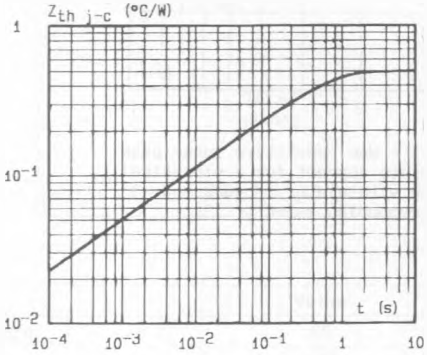


Fig.4 - Thermal transient impedance junction to case versus pulse duration.

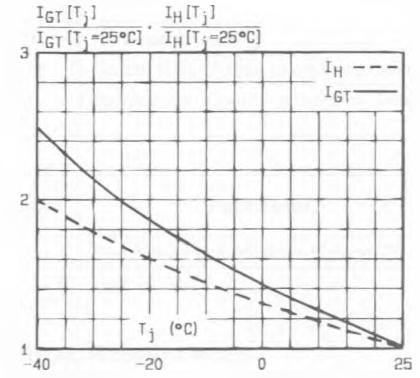


Fig.5 Relative variation of gate trigger current and holding current versus junction temperature.

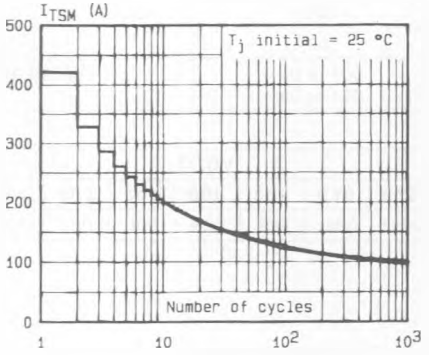


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

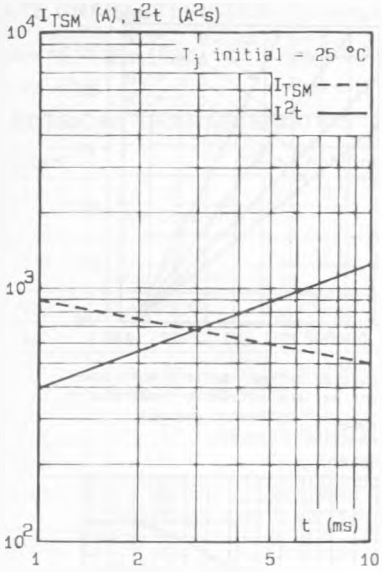


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t \leq 10ms$, and corresponding value of I^2t.

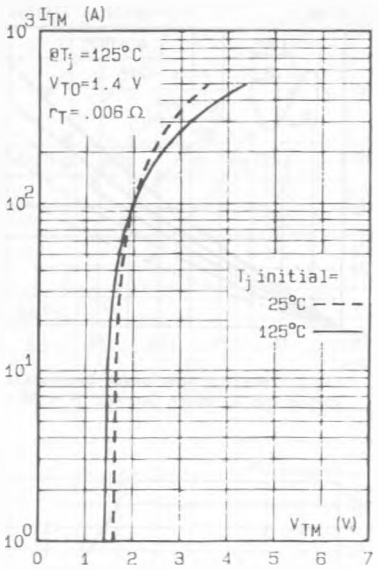


Fig.8 - On-state characteristic (maximum values).